

1A 40V Low VF(1.00mm)

Chip Information

Chip Size	1.00 x 1.00mm
Pad Size	0.89 x 0.89mm
Chip Quantity	10928 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Ti-Ag(For Solder)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	40	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR		V	
Average Forward Rectified Current	IF(AV)	1	A	
Peak Forward Surge Current	IFSM	30	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.385		0.350	V	IF=1A Ta=25degC
	VF2				V	
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	2	0.8		mA	VR=40V Ta=25degC
	IR2				mA	
	IR3				mA	
	IR4				mA	
Reverse Breakdown Voltage	BV	42	44		V	IR=1mA
Junction Capacitance	Cj				pF	
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back metal
YHW712	250 +/- 20um	Ti-Ni-Au (For Solder)

Note:

Designed For SSL12,SSL13,SSL14